



## Absolute Maximum Ratings $(T_A = 25^\circ\text{C}$ Unless Otherwise Noted)

Symbol	Parameter	Rating	Unit	
$V_{DSS}$	Drain-Source Voltage	30	V	
$V_{GSS}$	Gate-Source Voltage	$\pm 20$		
$I_D^a$	Continuous Drain Current ( $V_{GS}=10V$ )	$T_A=25^\circ\text{C}$	12	A
		$T_A=70^\circ\text{C}$	9.5	
$I_{DM}^a$	300 $\mu\text{s}$ Pulsed Drain Current ( $V_{GS}=10V$ )	40		
$I_S^a$	Diode Continuous Forward Current	3	A	
$I_{AR}^b$	Avalanche Current	22.5	A	
$E_{AR}^b$	Repetitive Avalanche Energy ( $L=0.3\text{mH}$ )	75	mJ	
$T_J$	Maximum Junction Temperature	150	$^\circ\text{C}$	
$T_{STG}$	Storage Temperature Range	-55 to 150		
$P_D^a$	Maximum Power Dissipation	$T_A=25^\circ\text{C}$	2.5	W
		$T_A=70^\circ\text{C}$	1.6	
$R_{\theta JA}^{a,c}$	Thermal Resistance-Junction to Ambient	$t \leq 10\text{s}$	50	$^\circ\text{C}/\text{W}$
$R_{\theta JL}$	Thermal Resistance-Junction to Lead	Steady State	25	$^\circ\text{C}/\text{W}$

Note a : Surface Mounted on  $1\text{in}^2$  pad area,  $t \leq 10\text{sec}$ .

Note b : UIS tested and pulse width limited by maximum junction temperature  $150^\circ\text{C}$  (initial temperature  $T_J=25^\circ\text{C}$ ).

Note c : Maximum under Steady State conditions is  $75^\circ\text{C}/\text{W}$ .

## Electrical Characteristics $(T_A = 25^\circ\text{C}$ Unless Otherwise Noted)

Symbol	Parameter	Test Conditions	APM4826K			Unit
			Min.	Typ.	Max.	
<b>Static Characteristics</b>						
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_{DS}=250\mu\text{A}$	30	-	-	V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS}=24V, V_{GS}=0V$	-	-	1	$\mu\text{A}$
		$T_J=85^\circ\text{C}$	-	-	30	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_{DS}=250\mu\text{A}$	1.3	1.8	2.5	V
$I_{GSS}$	Gate Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	$\pm 100$	nA
$R_{DS(ON)}^e$	Drain-Source On-state Resistance	$V_{GS}=10V, I_{DS}=12A$	-	9.5	12	m $\Omega$
		$V_{GS}=4.5V, I_{DS}=9A$	-	13.5	18	
<b>Diode Characteristics</b>						
$V_{SD}^e$	Diode Forward Voltage	$I_{SD}=3A, V_{GS}=0V$	-	0.75	1.3	V
$t_{rr}$	Reverse Recovery Time	$I_{SD}=12A, dI_{SD}/dt=100A/\mu\text{s}$	-	18	-	ns
$Q_{rr}$	Reverse Recovery Charge		-	11	-	nC

## Electrical Characteristics (Cont.) (T<sub>A</sub> = 25°C Unless Otherwise Noted)

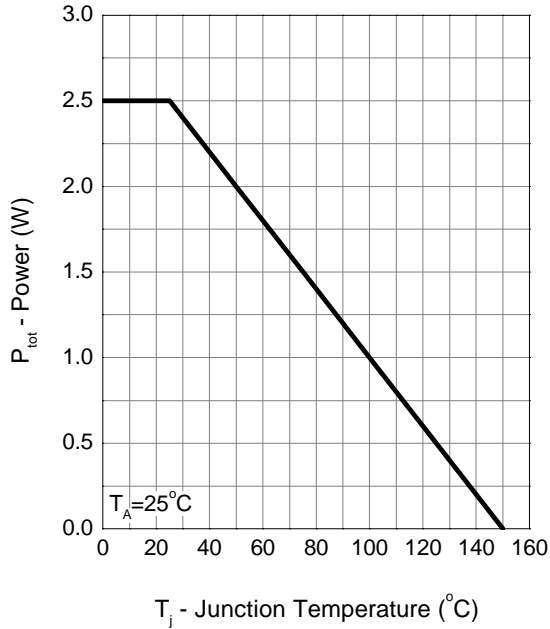
Symbol	Parameter	Test Conditions	APM4826K			Unit
			Min.	Typ.	Max.	
<b>Dynamic Characteristics <sup>f</sup></b>						
R <sub>G</sub>	Gate Resistance	V <sub>GS</sub> =0V, V <sub>DS</sub> =0V, F=1MHz	1	1.7	3	Ω
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> =0V, V <sub>DS</sub> =15V, Frequency=1.0MHz	-	1150	1400	pF
C <sub>oss</sub>	Output Capacitance		-	170	-	
C <sub>rss</sub>	Reverse Transfer Capacitance		-	135	-	
t <sub>d(ON)</sub>	Turn-on Delay Time	V <sub>DD</sub> =15V, R <sub>L</sub> =15Ω, I <sub>DS</sub> =1A, V <sub>GEN</sub> =10V, R <sub>G</sub> =6Ω	-	10	19	ns
t <sub>r</sub>	Turn-on Rise Time		-	12	23	
t <sub>d(OFF)</sub>	Turn-off Delay Time		-	30	55	
t <sub>f</sub>	Turn-off Fall Time		-	7	14	
<b>Gate Charge Characteristics <sup>f</sup></b>						
Q <sub>g</sub>	Total Gate Charge	V <sub>DS</sub> =15V, V <sub>GS</sub> =10V, I <sub>DS</sub> =12A	-	25.3	35	nC
Q <sub>gs</sub>	Gate-Source Charge		-	3.5	-	
Q <sub>gd</sub>	Gate-Drain Charge		-	6.5	-	

Note e : Pulse test ; pulse width ≤ 300μs, duty cycle ≤ 2%.

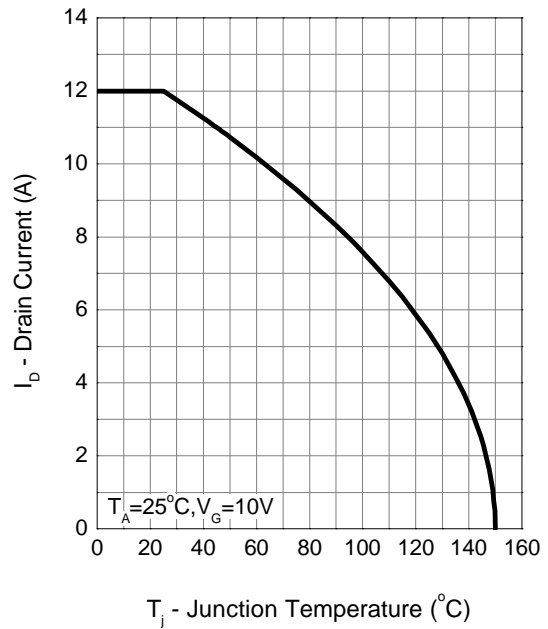
Note f : Guaranteed by design, not subject to production testing.

## Typical Operating Characteristics

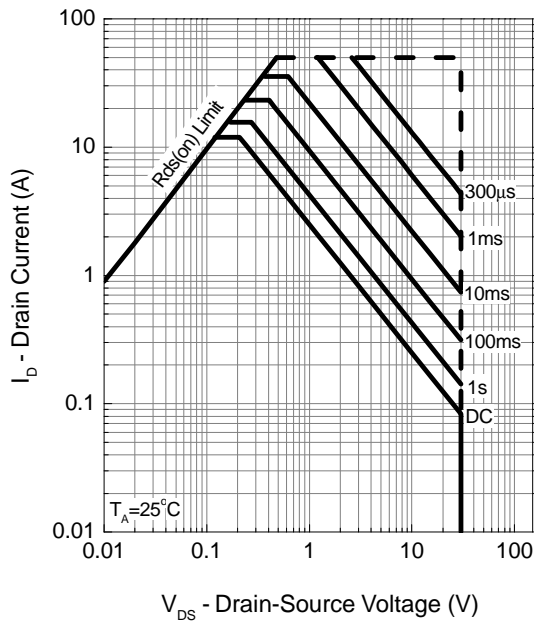
Power Dissipation



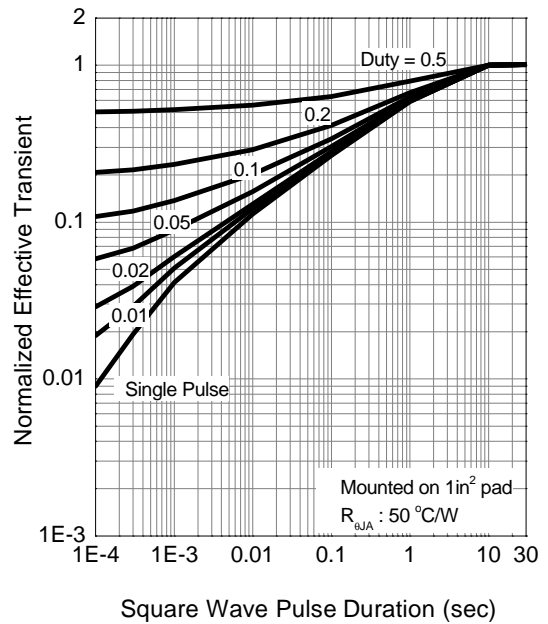
Drain Current



Safe Operation Area

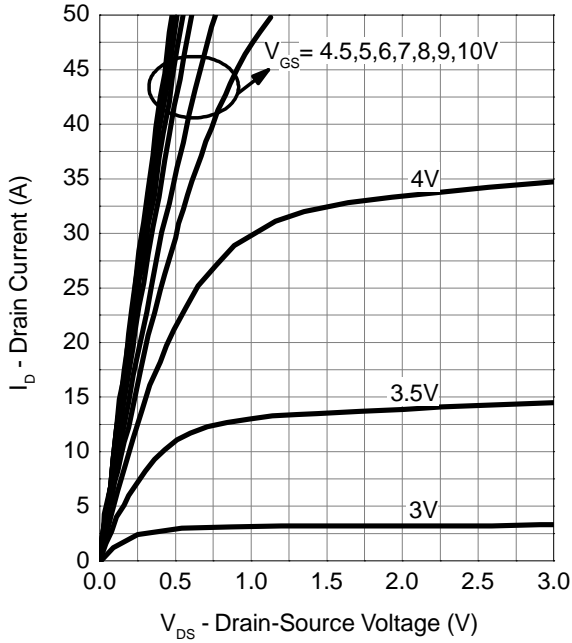


Thermal Transient Impedance

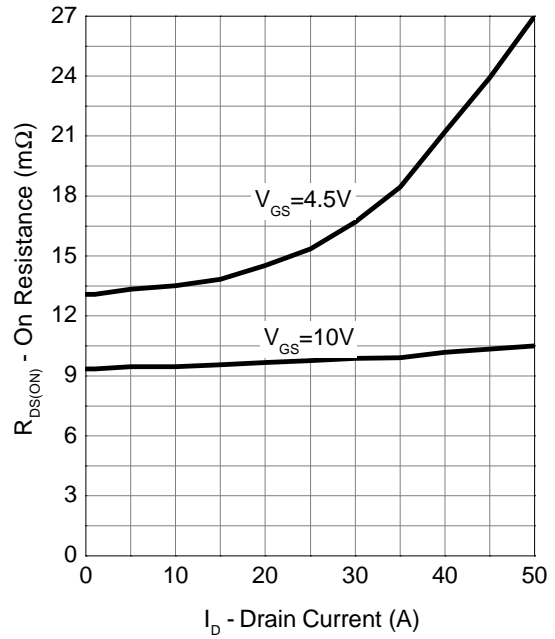


Typical Operating Characteristics (Cont.)

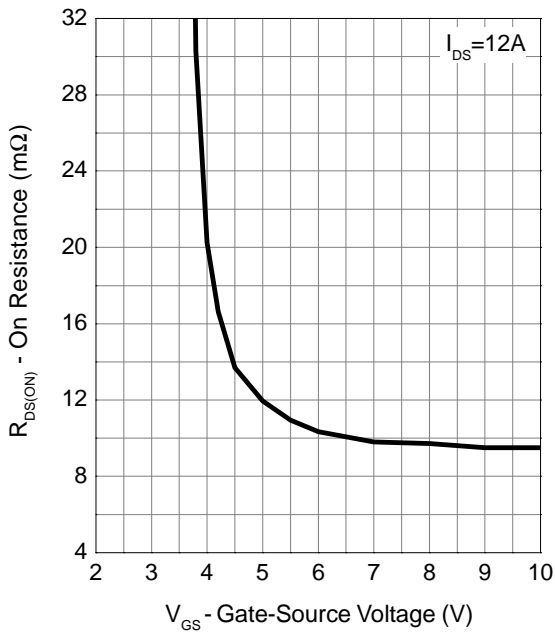
Output Characteristics



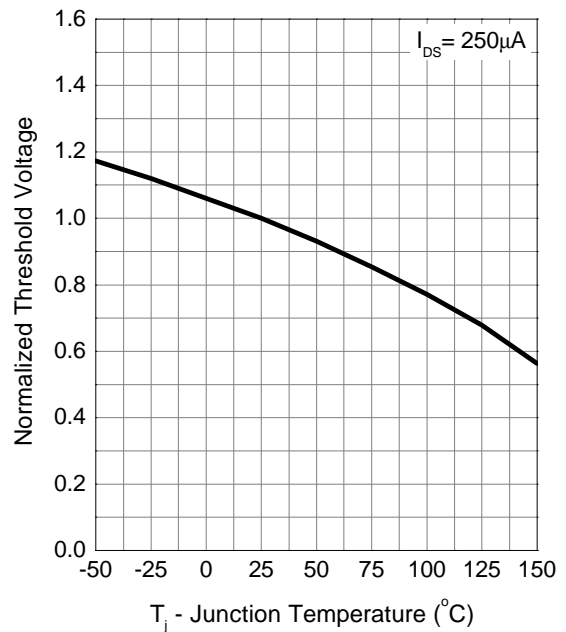
Drain-Source On Resistance



Gate-Source On Resistance

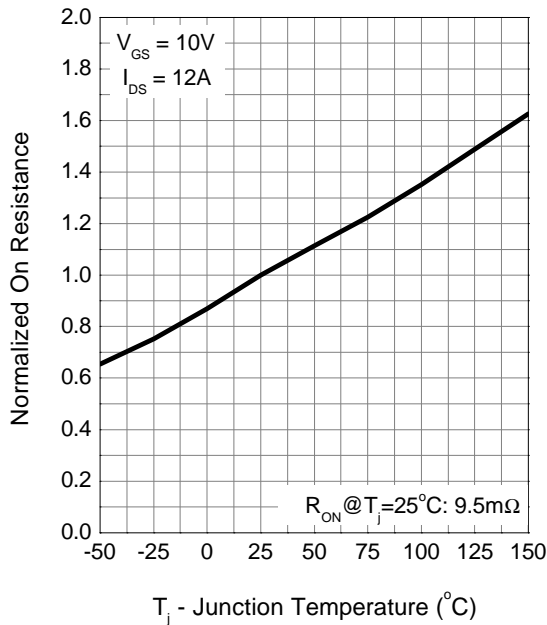


Gate Threshold Voltage

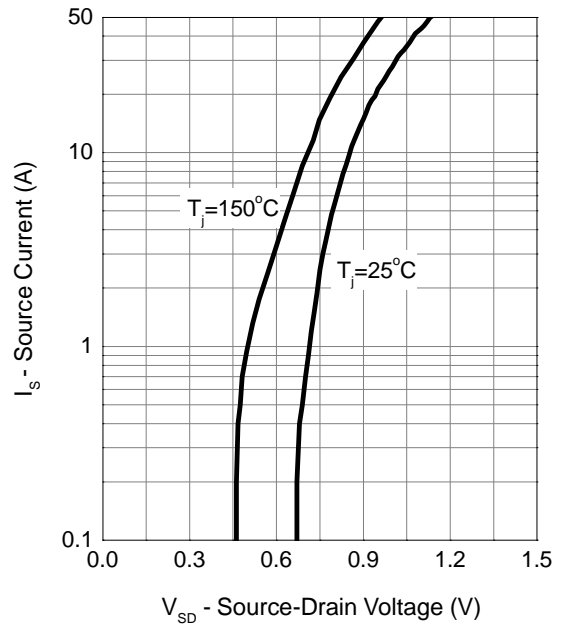


Typical Operating Characteristics (Cont.)

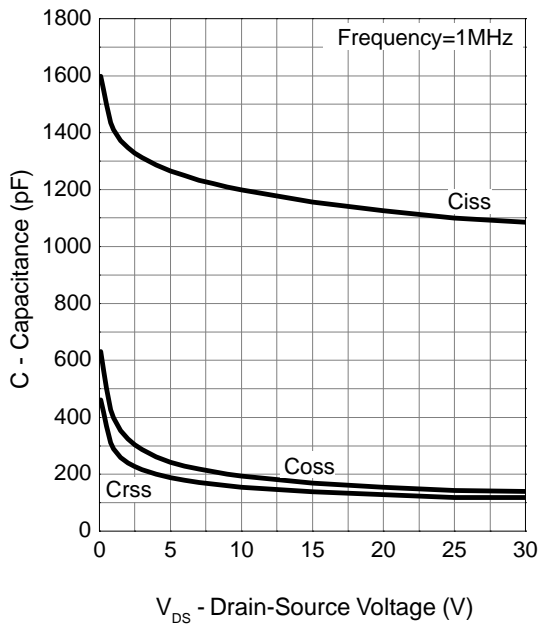
Drain-Source On Resistance



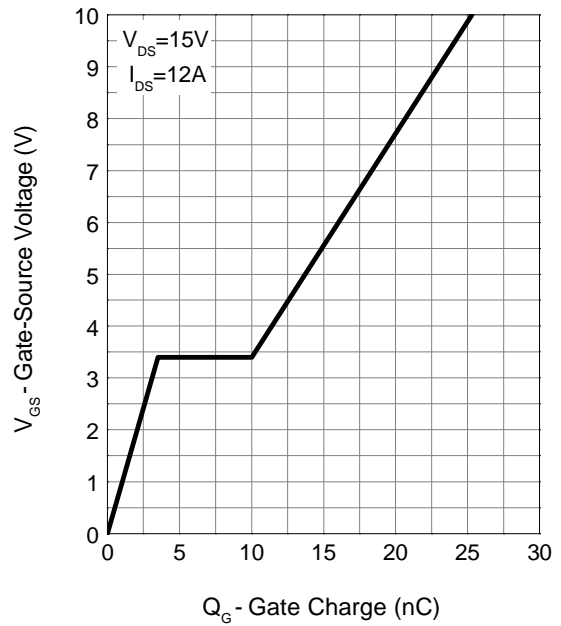
Source-Drain Diode Forward



Capacitance

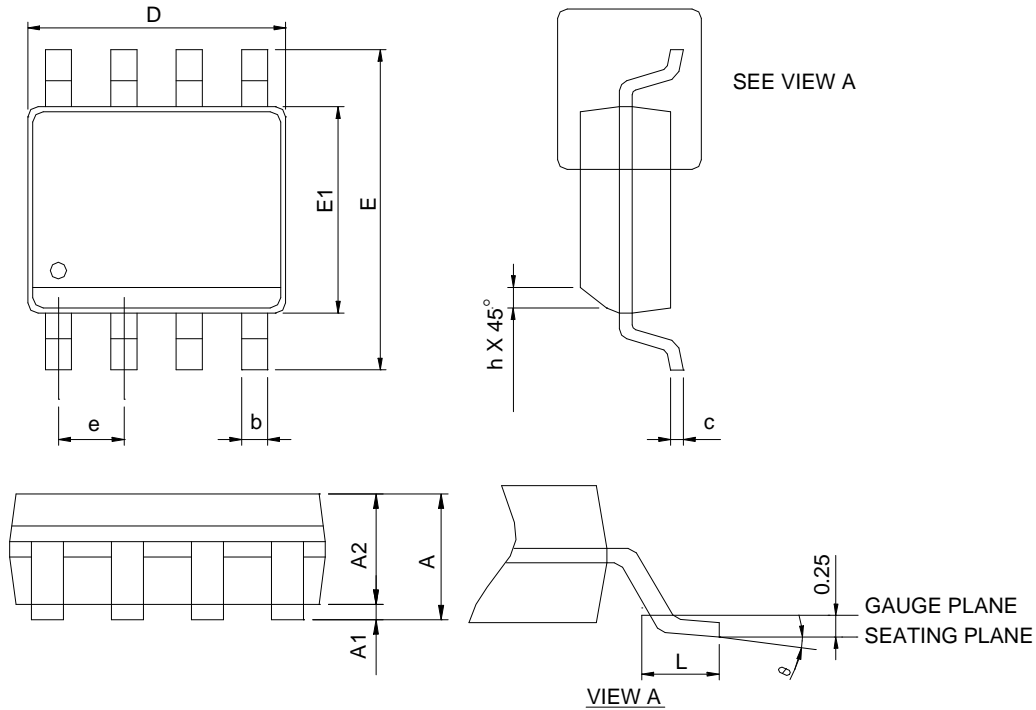


Gate Charge



Package Information

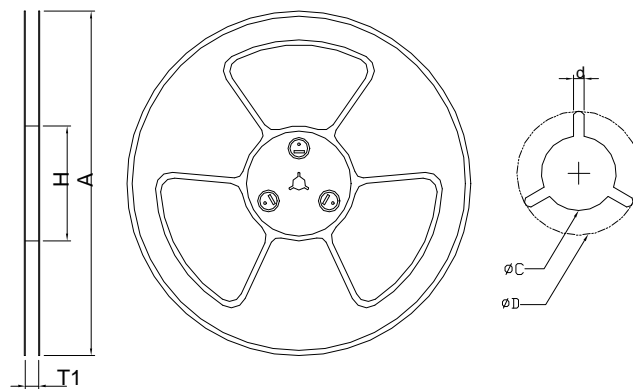
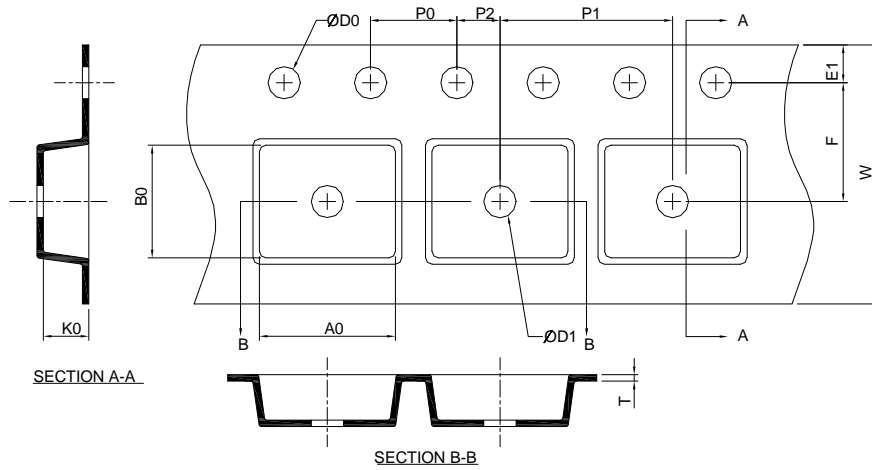
SOP-8



SYMBOL	SOP-8			
	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A		1.75		0.069
A1	0.10	0.25	0.004	0.010
A2	1.25		0.049	
b	0.31	0.51	0.012	0.020
c	0.17	0.25	0.007	0.010
D	4.80	5.00	0.189	0.197
E	5.80	6.20	0.228	0.244
E1	3.80	4.00	0.150	0.157
e	1.27 BSC		0.050 BSC	
h	0.25	0.50	0.010	0.020
L	0.40	1.27	0.016	0.050
$\theta$	0°	8°	0°	8°

- Note: 1. Follow JEDEC MS-012 AA.  
 2. Dimension "D" does not include mold flash, protrusions or gate burrs. Mold flash, protrusion or gate burrs shall not exceed 6 mil per side.  
 3. Dimension "E" does not include inter-lead flash or protrusions. Inter-lead flash and protrusions shall not exceed 10 mil per side.

### Carrier Tape & Reel Dimensions



Application	A	H	T1	C	d	D	W	E1	F
SOP-8	330.0 ±2.00	50 MIN.	12.4+2.00 -0.00	13.0+0.50 -0.20	1.5 MIN.	20.2 MIN.	12.0 ±0.30	1.75 ±0.10	5.5 ±0.05
	P0	P1	P2	D0	D1	T	A0	B0	K0
	4.0 ±0.10	8.0 ±0.10	2.0 ±0.05	1.5+0.10 -0.00	1.5 MIN.	0.6+0.00 -0.40	6.40 ±0.20	5.20 ±0.20	2.10 ±0.20

(mm)

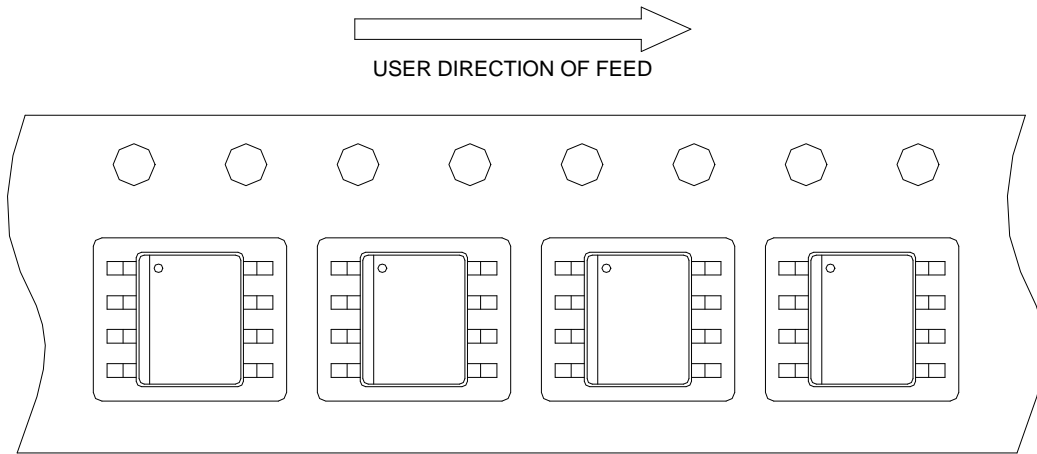
### Devices Per Unit

Package Type	Unit	Quantity
SOP-8	Tape & Reel	2500

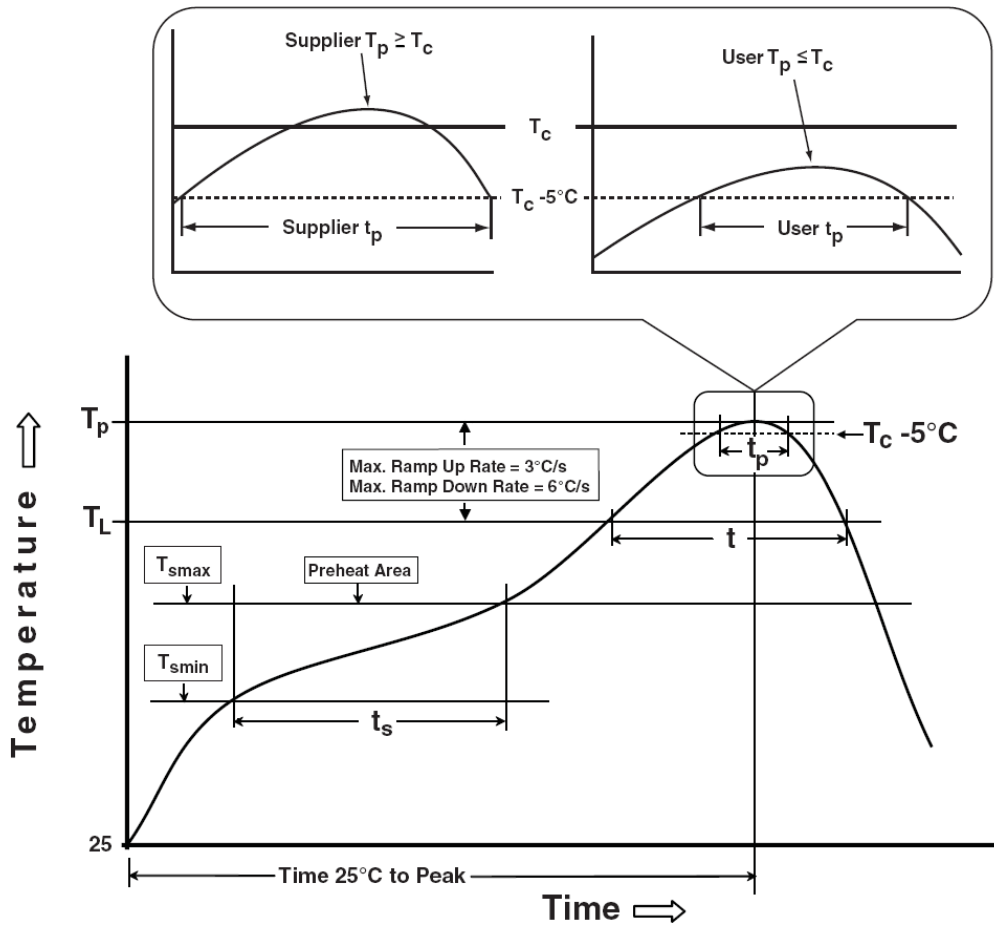


## Taping Direction Information

SOP-8



## Classification Profile



## Classification Reflow Profiles

Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
<b>Preheat &amp; Soak</b>		
Temperature min ( $T_{smin}$ )	100 °C	150 °C
Temperature max ( $T_{smax}$ )	150 °C	200 °C
Time ( $T_{smin}$ to $T_{smax}$ ) ( $t_s$ )	60-120 seconds	60-120 seconds
Average ramp-up rate ( $T_{smax}$ to $T_p$ )	3 °C/second max.	3°C/second max.
Liquidous temperature ( $T_L$ )	183 °C	217 °C
Time at liquidous ( $t_L$ )	60-150 seconds	60-150 seconds
Peak package body Temperature ( $T_p$ )*	See Classification Temp in table 1	See Classification Temp in table 2
Time ( $t_p$ )** within 5°C of the specified classification temperature ( $T_c$ )	20** seconds	30** seconds
Average ramp-down rate ( $T_p$ to $T_{smax}$ )	6 °C/second max.	6 °C/second max.
Time 25°C to peak temperature	6 minutes max.	8 minutes max.
* Tolerance for peak profile Temperature ( $T_p$ ) is defined as a supplier minimum and a user maximum.		
** Tolerance for time at peak profile temperature ( $t_p$ ) is defined as a supplier minimum and a user maximum.		

Table 1. SnPb Eutectic Process – Classification Temperatures ( $T_c$ )

Package Thickness	Volume mm <sup>3</sup> <350	Volume mm <sup>3</sup> ≥350
<2.5 mm	235 °C	220 °C
≥2.5 mm	220 °C	220 °C

Table 2. Pb-free Process – Classification Temperatures ( $T_c$ )

Package Thickness	Volume mm <sup>3</sup> <350	Volume mm <sup>3</sup> 350-2000	Volume mm <sup>3</sup> >2000
<1.6 mm	260 °C	260 °C	260 °C
1.6 mm – 2.5 mm	260 °C	250 °C	245 °C
≥2.5 mm	250 °C	245 °C	245 °C

## Reliability Test Program

Test item	Method	Description
SOLDERABILITY	JESD-22, B102	5 Sec, 245°C
HOLT	JESD-22, A108	1000 Hrs, Bias @ 125°C
PCT	JESD-22, A102	168 Hrs, 100%RH, 2atm, 121°C
TCT	JESD-22, A104	500 Cycles, -65°C~150°C

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## Customer Service

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